

PRODUCT RELIABILITY REPORT FOR

DS4250, Rev A1

Maxim Integrated Products

4401 South Beltwood Parkway Dallas, TX 75244-3292

Prepared by:

Don Lipps
Staff Reliability Engineer
Maxim Integrated Products
4401 South Beltwood Pkwy.
Dallas, TX 75244-3292

Email: don.lipps@maxim-ic.com ph: 972-371-3739

fax: 972-371-6016

Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Maxim products:

In addition, Maxim's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

```
AfT = \exp((Ea/k)^*(1/Tu - 1/Ts)) = tu/ts
```

AfT = Acceleration factor due to Temperature

tu = Time at use temperature (e.g. 55°C)

ts = Time at stress temperature (e.g. 125°C)

k = Boltzmann's Constant (8.617 x 10-5 eV/°K)

Tu = Temperature at Use (°K)

Ts = Temperature at Stress (°K)

Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

```
AfV = exp(B*(Vs - Vu))
```

AfV = Acceleration factor due to Voltage

Vs = Stress Voltage (e.g. 7.0 volts)

Vu = Maximum Operating Voltage (e.g. 5.5 volts)

B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

```
Fr = X/(ts * AfV * AfT * N * 2)
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X = Chi-Sq statistical upper limit

N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE: MTTF (YRS): 31045 FITS: 3.7

DEVICE HOURS: 323640 FAILS: 0

Only data from Operating Life or similar stresses are used for this calculation.

The parameters used to calculate this failure rate are as follows:

Cf: 60% Ea: 0.7 B: 0 Tu: 25 °C Vu: 3.5 Volts

The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. "*" after DATE CODE denotes specific product data and SEQ No. to identify specific line items in the report for comments when required.

Device Information:

Process: SVL F60 Process.

Passivation: Laser/TEOS Ox - Pass/Nit -PreLP+GenLP

Die Size: 48 x 104

Number of Transistors: 0

Interconnect: Aluminum / 0.5% Copper

Gate Oxide Thickness: <160 A

ELECTRICAL CHARACTERIZATION										
DESCRIPTION	DATE CODE/SEQ		CONDITION		READPOINT		FAILS	FA#		
ESD SENSITIVITY	0744	* 1	EOS/ESD S5.1 HBM 500 VOLTS	1	PUL'S	3	0			
ESD SENSITIVITY	0744	* 2	EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	3	0			
ESD SENSITIVITY	0744	* 3	EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	3	0			
ESD SENSITIVITY	0744	* 4	EOS/ESD S5.1 HBM 4000 VOLTS	1	PUL'S	3	0			
ESD SENSITIVITY	0744	* 5	EOS/ESD S5.1 HBM 8000 VOLTS	1	PUL'S	3	0			
LATCH-UP	0744	* 6	JESD78, I-TEST 125C			6	0			
LATCH-UP	0744	* 7	JESD78, V-SUPPLY TEST 125C			6	0			
					Total:		0			

0	PERATING LIFE							
DE	SCRIPTION	DATE CODE/SEQ	CONDITION	READ	POINT	QTY	FAILS	FA#
Н	GH TEMP OP LIFE	0705	125C, 3.6 VOLTS	1000	HRS	45	0	
Н	GH TEMP OP LIFE	0707	125C, 3.6 VOLTS	1000	HRS	45	0	
Н	GH TEMP OP LIFE	0707	125C, 3.6 VOLTS	1000	HRS	45	0	
Н	GH TEMP OP LIFE	0722	125C, 3.5 VOLTS	1000	HRS	45	0	
Н	GH TEMP OP LIFE	0722	105C, 3.5 VOLTS	1000	HRS	45	0	

FAILURE RATE:		MTTF	(YRS):	31045	FITS:		3.7			
						-	Γotal:			0
HIGH TEMP OP LIFE	0744	* 1	* 1 105C, 3.5 VOLTS			1000	HRS	4	15	0
HIGH TEMP OP LIFE	0738		125C, 3.5 V	OLTS		1000	HRS	4	15	0
HIGH TEMP OP LIFE	0726		125C, 3.5 V	OLTS		192	HRS	2	15	0

323640

FAILS:

0

DEVICE HOURS: